

GORDANA
LASTOVICKA-MEDIN

COST ACTION CA24131

European Network for radiation-detection based Research and
Innovation addressing increasing societal CHallenges (ENRICH)



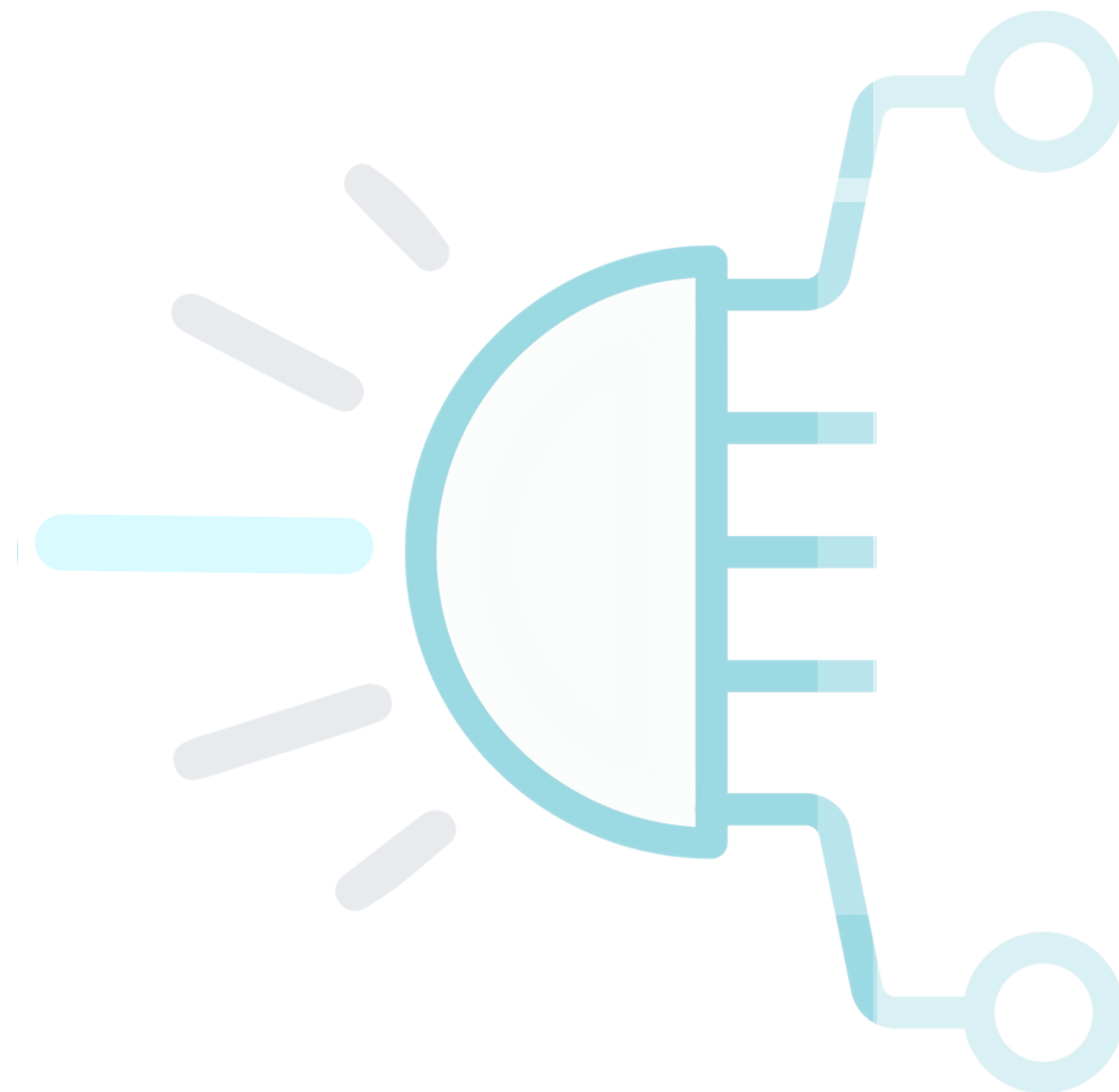
ENRICH

3D IME-CAS Si Radiation Detectors with Gain Driven by Geometry

Gordana Lastovicka-Medin, 1st ENRICH Cost Annual Meeting,
14-16 July 2026, Krakow

Overview

- ☐ Introduction
- ☐ Timing detectors
- ☐ 3D IME-CAS with gain (proof of concept)
- ☐ Future direction



DRD3

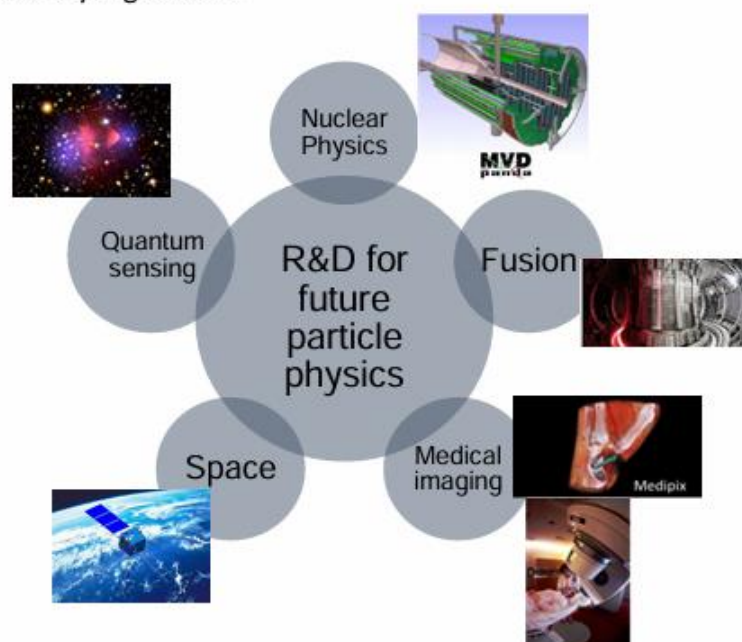
(R&D on Solid-state Detector Technologies)

Objectives of the collaboration

DRD3

The DRD3 collaboration has the dual purpose of pursuing the realization of the **strategic developments** outlined in the ECFA road map and **promoting blue-sky R&D** in the field of solid-state detectors including the synergies with other fields of science where charged particle detection is a key ingredient.

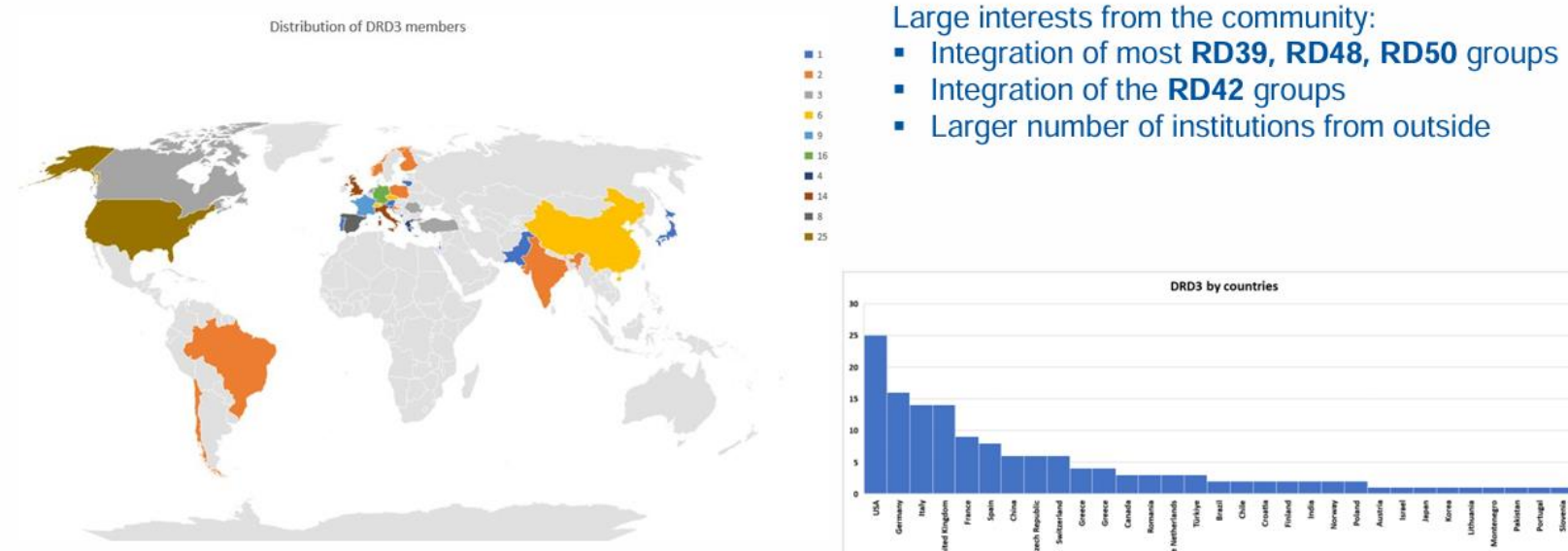
Particle Physics



The DRD3 collaboration

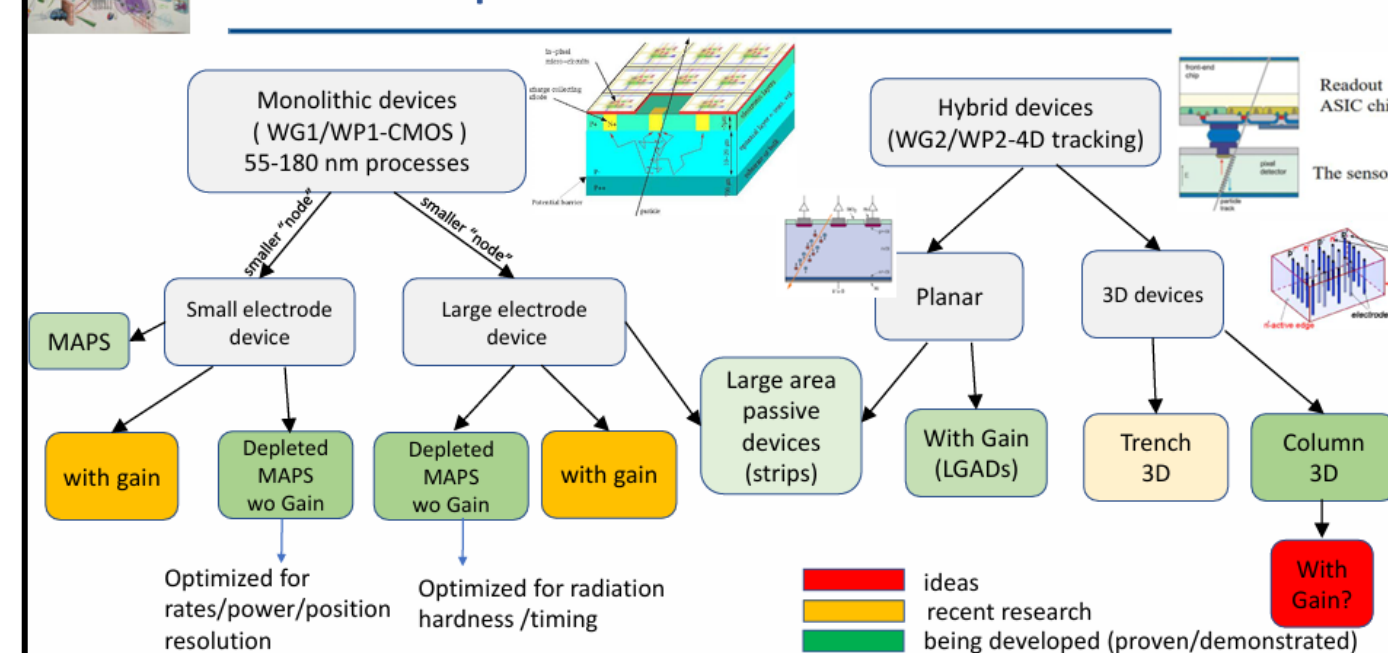
DRD3

A large collaboration on semiconductor has been formed at CERN to guide and steer the developments of semiconductor **sensor developments in the next decades**. 145 Institutes currently involved with 700+ people



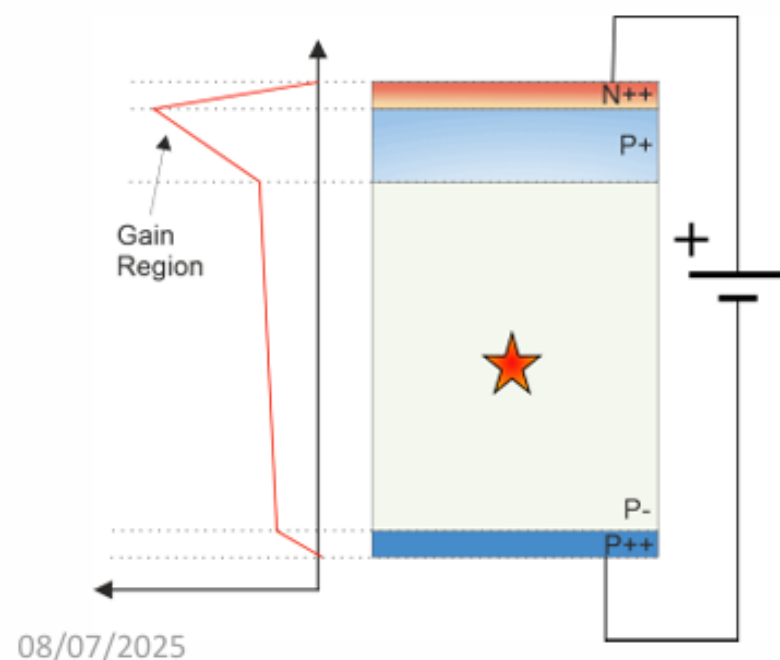
Paths of present silicon sensor R&D

DRD3



Low Gain Avalanche Detector

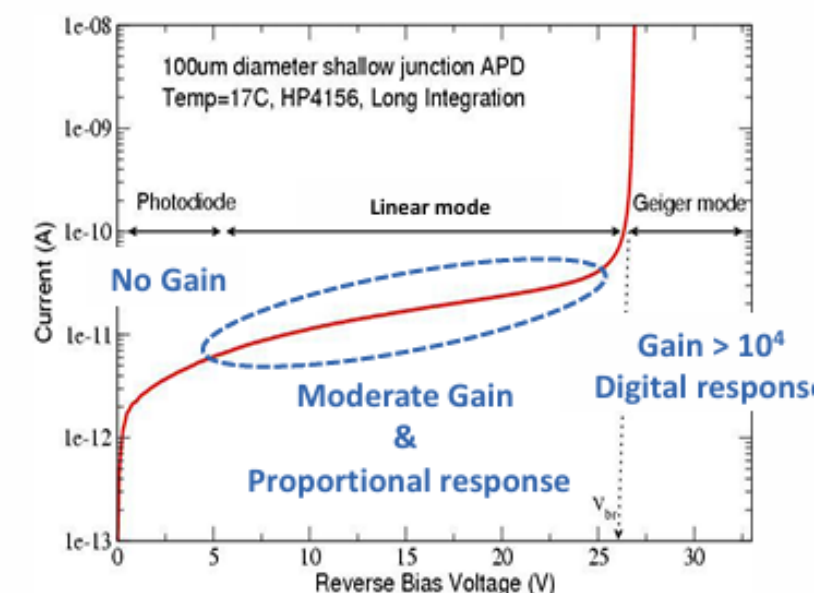
- Proposed by IMB-CNM in 2014
- Proportional response (linear mode operation)
- Better sensitivity (Gain)
 - S/N ratio increased
 - Excellent timing resolution (~ 30 ps)
 - MIP detection for HEP
- Thin detector integration with the same signal and higher collection efficiency



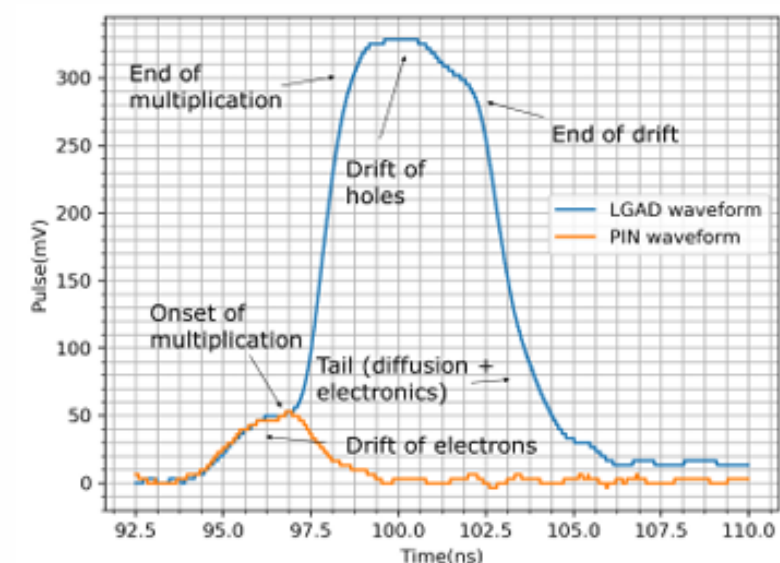
08/07/2025

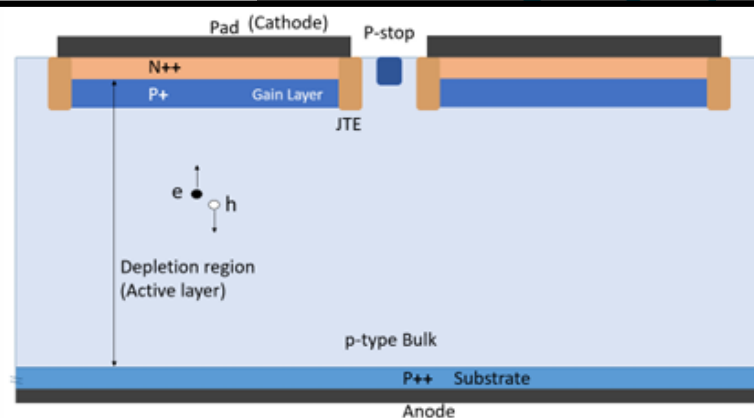
Original paper

G. Pellegrini, et al., Technology developments and first measurements of Low Gain Avalanche Detectors (LGAD) for high energy physics applications, Nucl. Instrum. Methods A 765 (2014) 12.



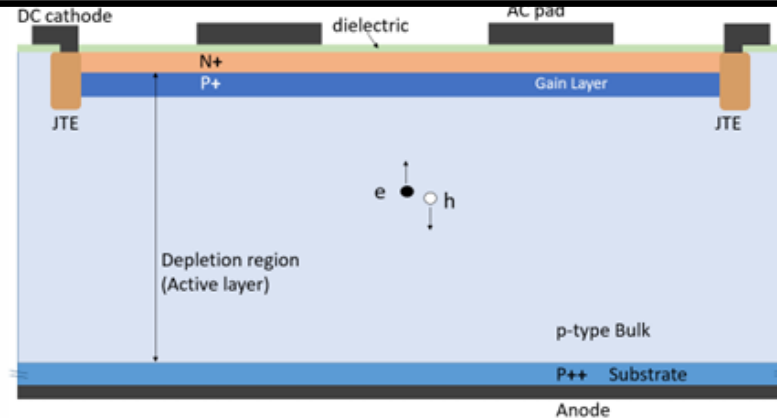
[1] A.G. Stewart et al. in Proc. of SPIE, Vol. 6119, 2006





LGAD (Low-Gain Avalanche Diode)

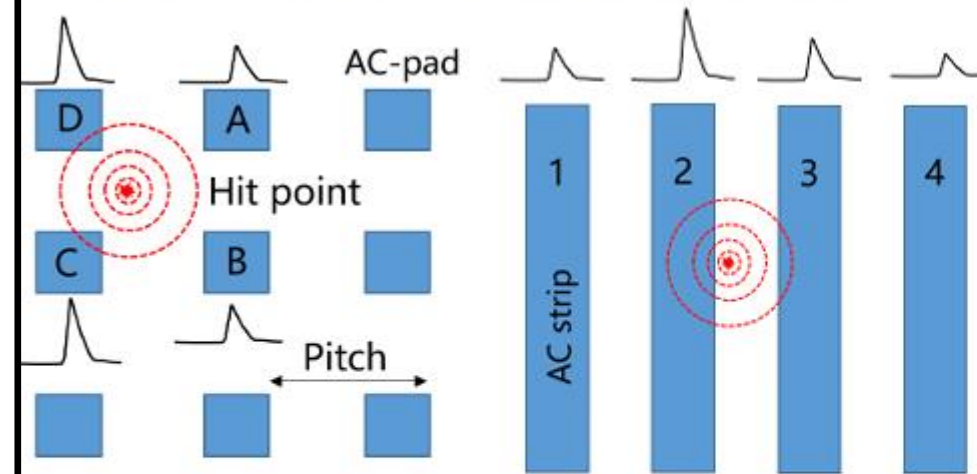
- The read-out electronics is connected to n++ layer
- Time resolution ~ 30ps
- Position resolution: pixel size/ $\sqrt{12}$
- Radiation hardness: $10^{15} \sim 10^{16} n_{eq}/cm^2$



AC-LGAD (AC-coupled LGAD)

- Metal AC-pads separated from the n+ layer by a thin dielectric (Si_3N_4 , SiO_2)
- no dead zone (100% fill factor)
- Time resolution ~ 30ps
- **Position resolution: 5~10 μm**
- Radiation hardness: $10^{15} \sim 10^{16} n_{eq}/cm^2$

AC-LGAD: two layout schemes for AC-pads



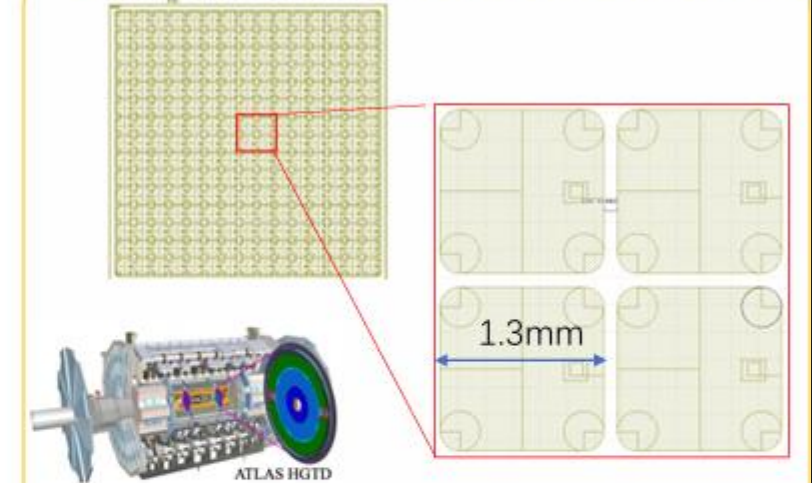
Pixels AC-LGAD:

- Position information: 1 layer (x,y)
- Bump bonding

Strips AC-LGAD:

- Lower readout electronics, no bump bonding
- Position information: 2 layers for (x,y)

DC-LGAD:
15x15 LGAD for ATLAS HGTD project

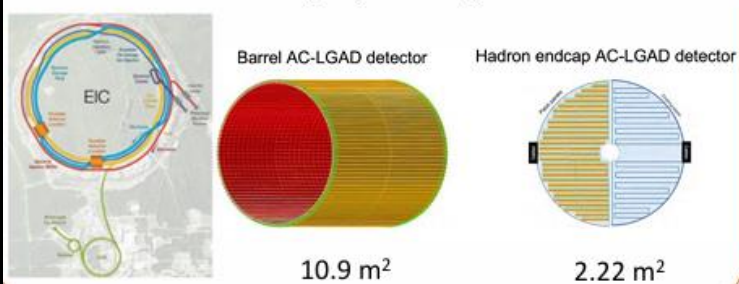


- Dead zone : ~0.1mm
- Pixel size: 1.3mm

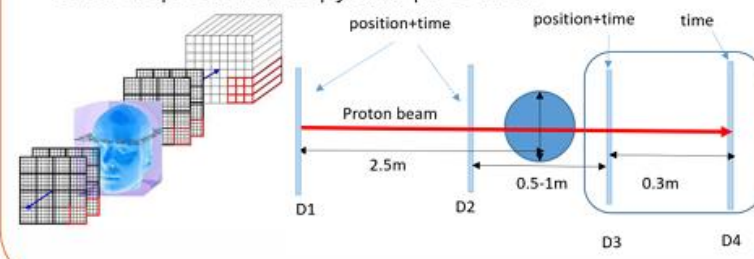
Smaller Pixel LGADs -> Lower fill factor

3

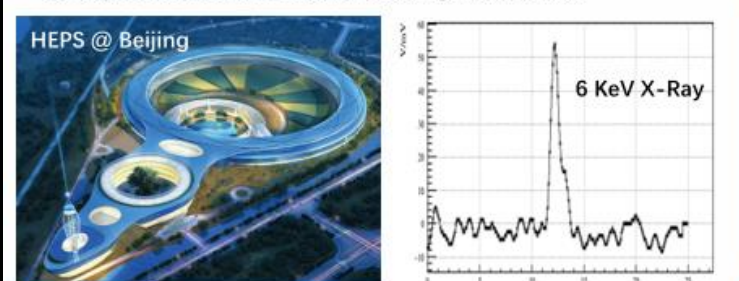
Electron-Ion Collider (EIC): Timing-tracker



Nuclear Medicine Instruments:
Such as proton therapy and proton CT



X-ray detectors @ advanced light sources



other applications

- Beam Telescope for Beam Test Platform
- LiDAR: Positioning and Navigation
- Track and time detectors in other particle physics and nuclear physics experiments
- ...

LGAD based Timing Tracker Development for Future Electron Collider

MEI ZHAO(IHEP)

DRD3 WG2 Project: LGAD based timing tracker development for future electron collider <https://cds.cern.ch/record/2918306>

ON BEHALF OF GROUPS IN THE PROJECT



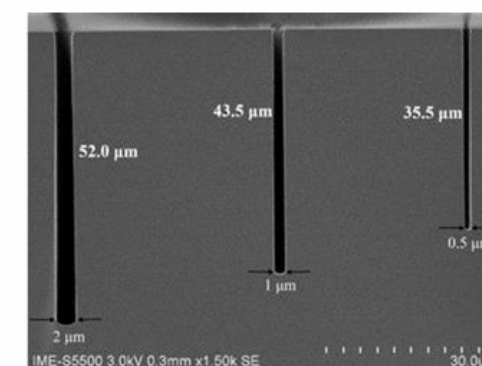
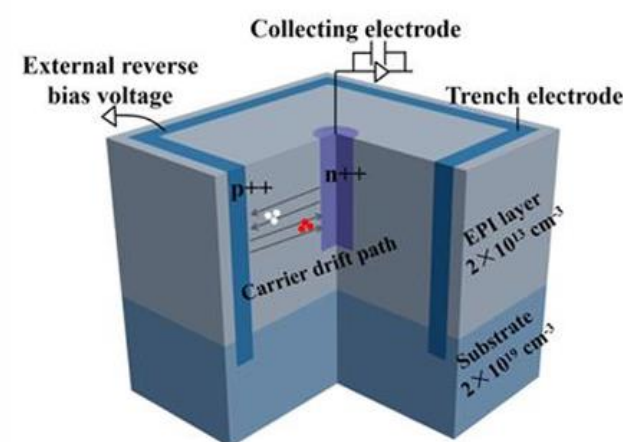
2025/6/4

3RD DRD3 WEEK ON SOLID STATE DETECTORS R&D, 2-6 JUN 2025, NIKHEF, AMSTERDAM

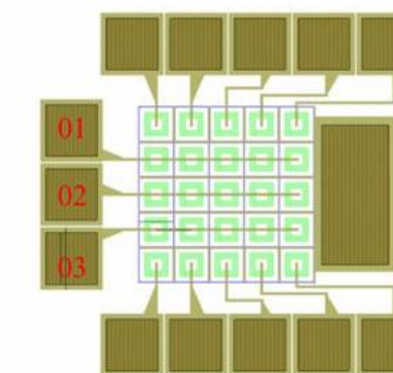


AC-LGAD - 4D detector (position + time)
16 μm -patial resolution, 10-20 ps of timing resolution

Motivation of the project



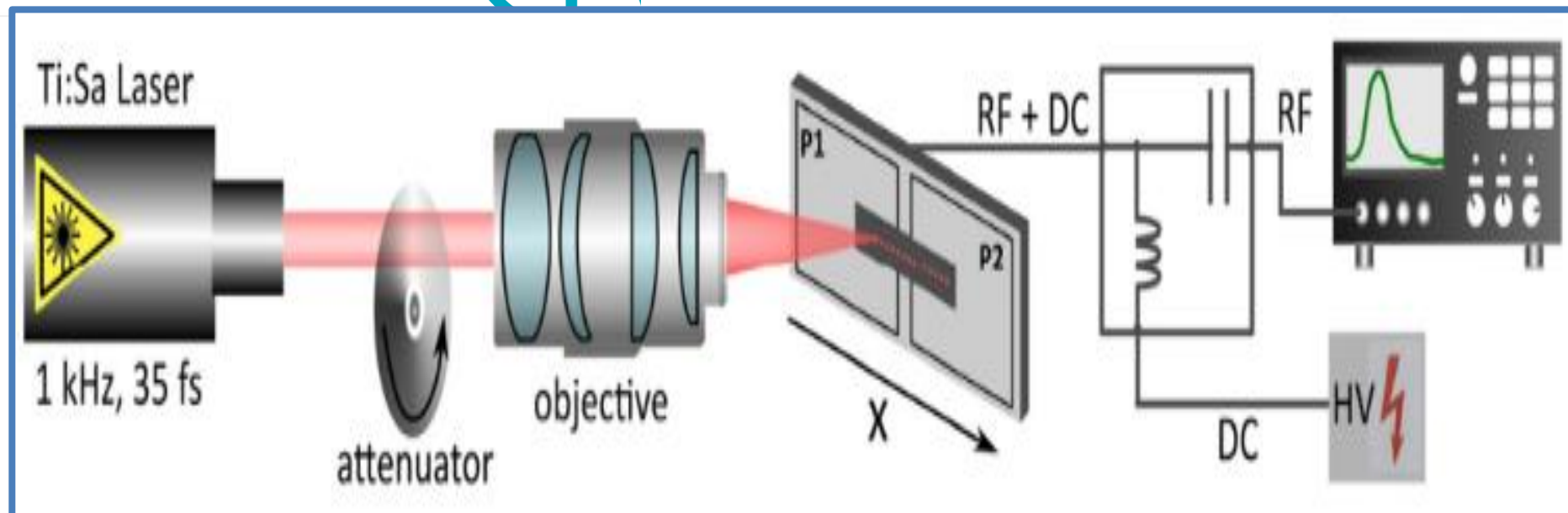
Workhorse (5x5 matrix)



The IME-3D process can reach **aspect ratio of >70:1** which allows **columns of as narrow as 0.5 mm** penetrating 30-35 mm in the silicon – thin means much less capacitance (noise/power consumption at the same speed)

- The runs in the proposal include also structures for other uses – not particle physics only (X-ray detectors, Micro-dosimetry, Particle detectors)
- It is clear that improvement of aspect ratio to >70:1 allows manufacturing of very narrow columns <0.5 mm which can **be seen as proportional wire counter** – most of the work in the project done with this structure by different groups in the project (IME, IHEP, LDU, USTC, NIKHEF, UCG-ELI, JSI, Sheffield)

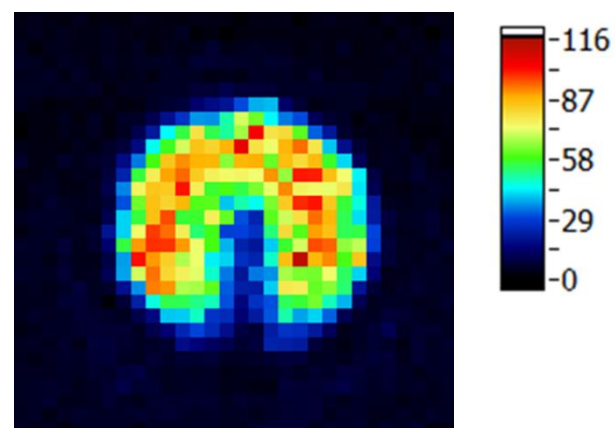




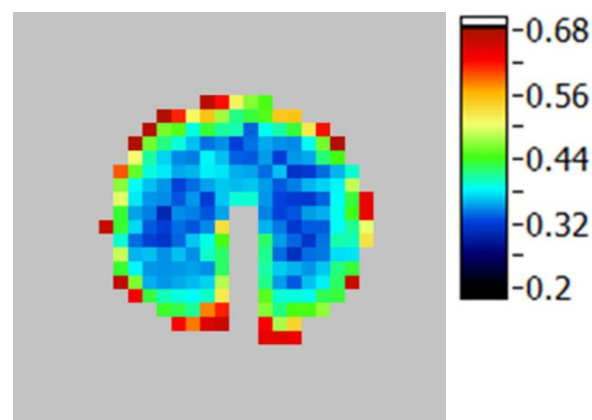
Place	ELI Beamlines
Operational modes	Single and two photon absorption (SPA and TPA)
Pulse energy on sample	Variable by ND filters (accuracy: 0.2 pJ) 800 nm (SPA), 1550 nm (TPA)
Wavelength	1550 nm, ~ 150 fs 800 nm, ~ 50 fs
Pulse width in sensor	
Focus waist radius	0.85 μm (SPA), 1.5 μm (TPA)
Rayleigh length	3.31 μm (SPA), 7.74 μm (TPA)
Sample cooling	Down to -25 deg. C
Sample movement	X, Y, Z
Bias voltage	up to or > 720 V
Detection	6 GHz (20 GSa) oscilloscope and leakage current measurement (accuracy: 0.1 μA)

TPA focal point at 10 μm , 20 pJ, 60 V

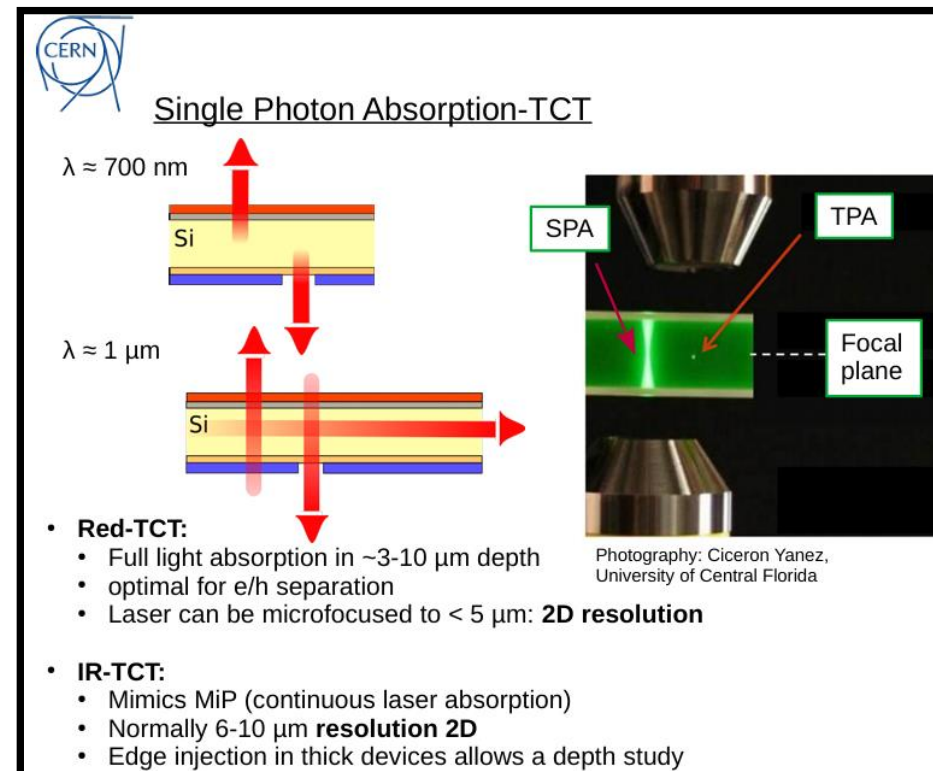
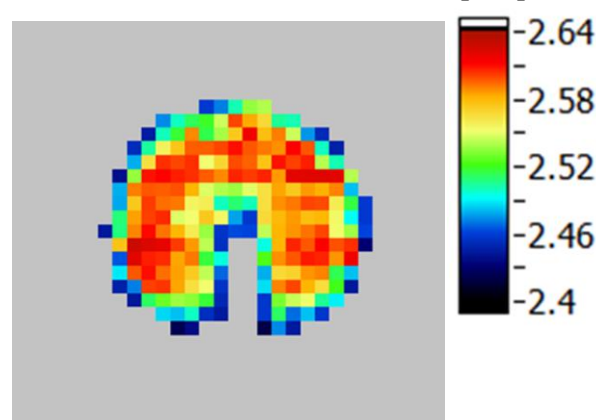
2D of charge distribution



2D of Rise Time [ns]



2D of Time of Arrival [ns]

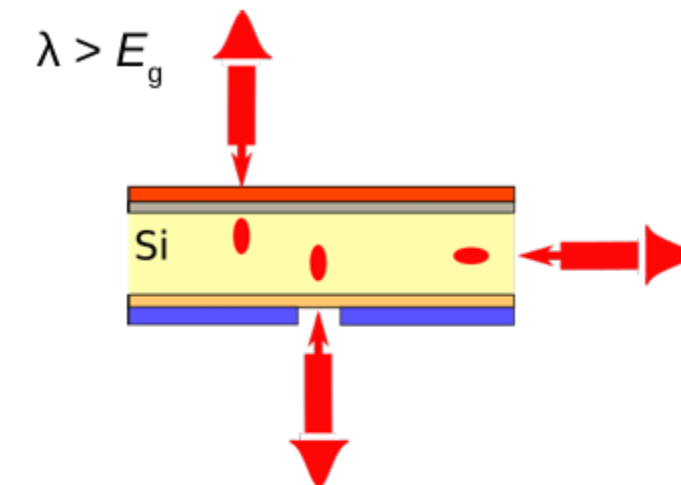


Two Photon Absorption-TCT

- 3D resolution tool to scan silicon devices**



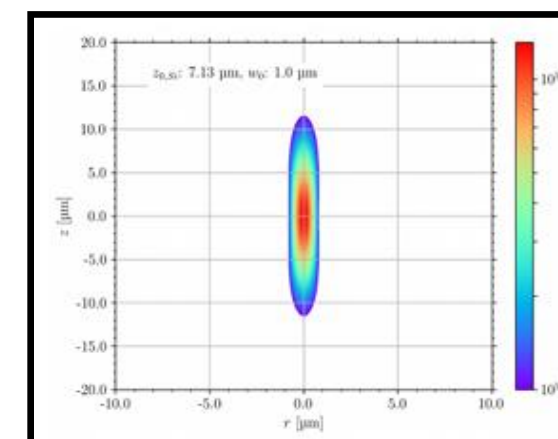
Two Photon Absorption-TCT



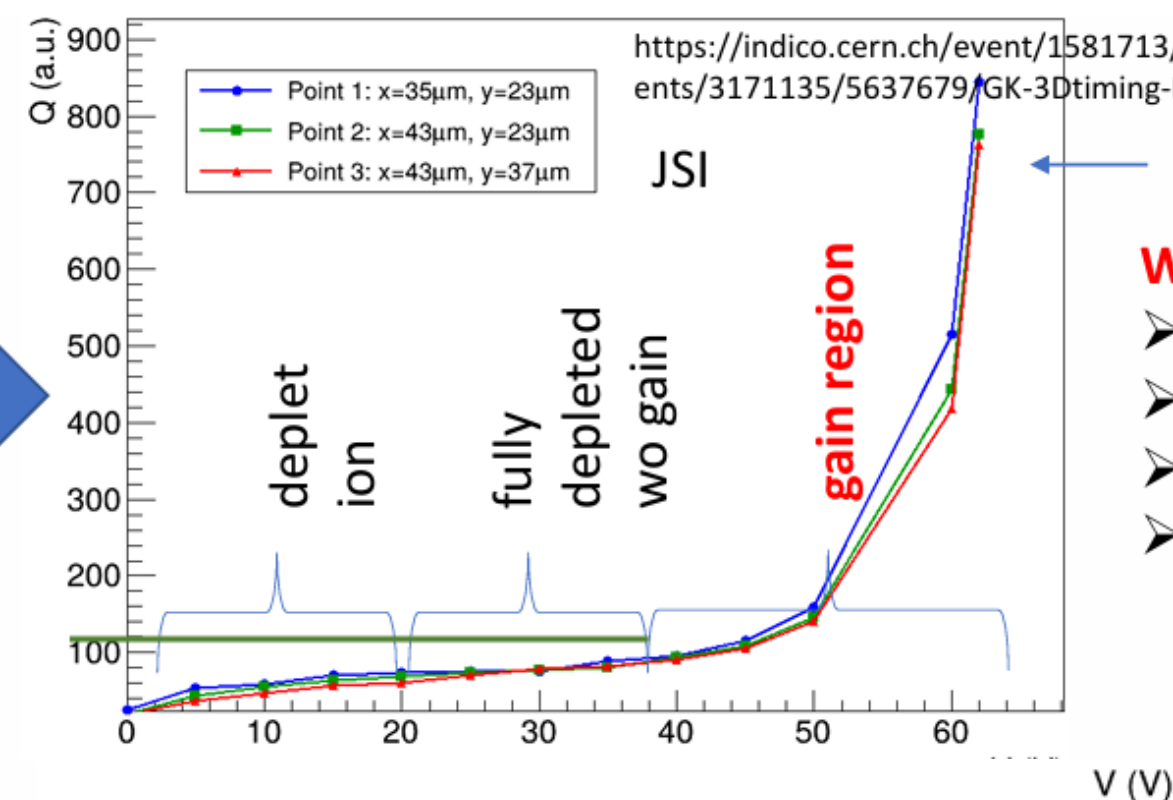
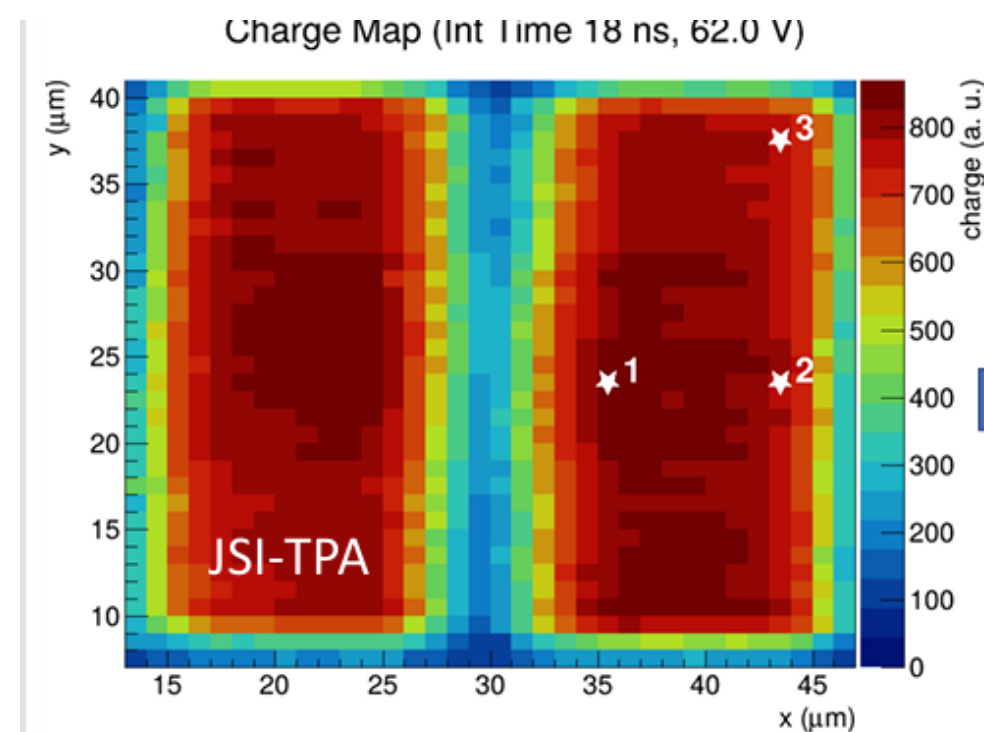
- TPA** excites charge carriers into the CB
- Non-linear effect, strongly depends on intensity
- Coincidence in time and space needed

→ only excitation around focal point

- 3D resolution tool to scan silicon devices**



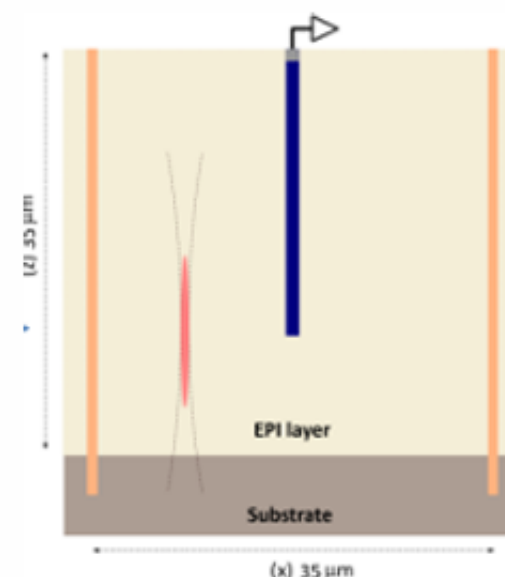
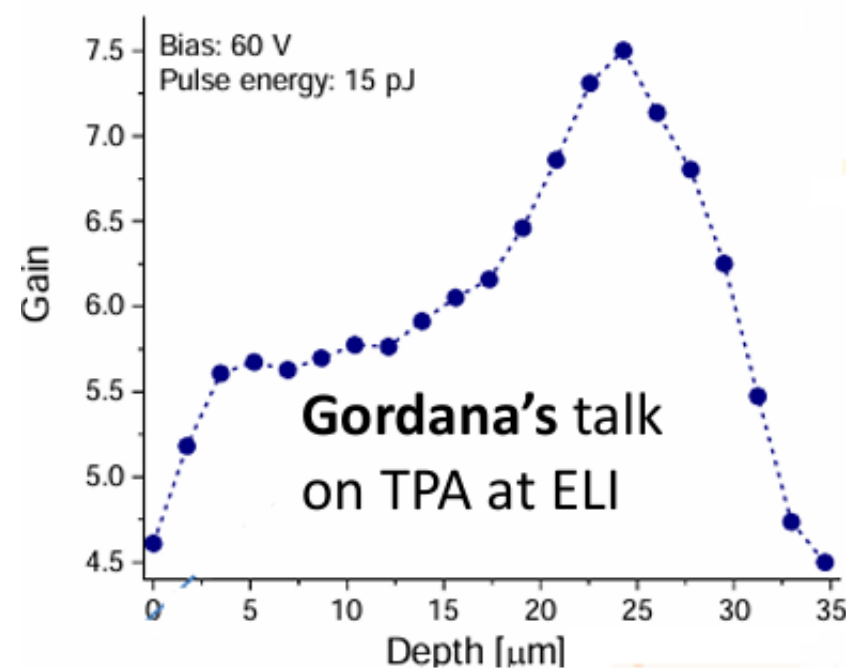
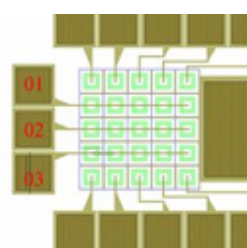
Hunting for the gain



breakdown

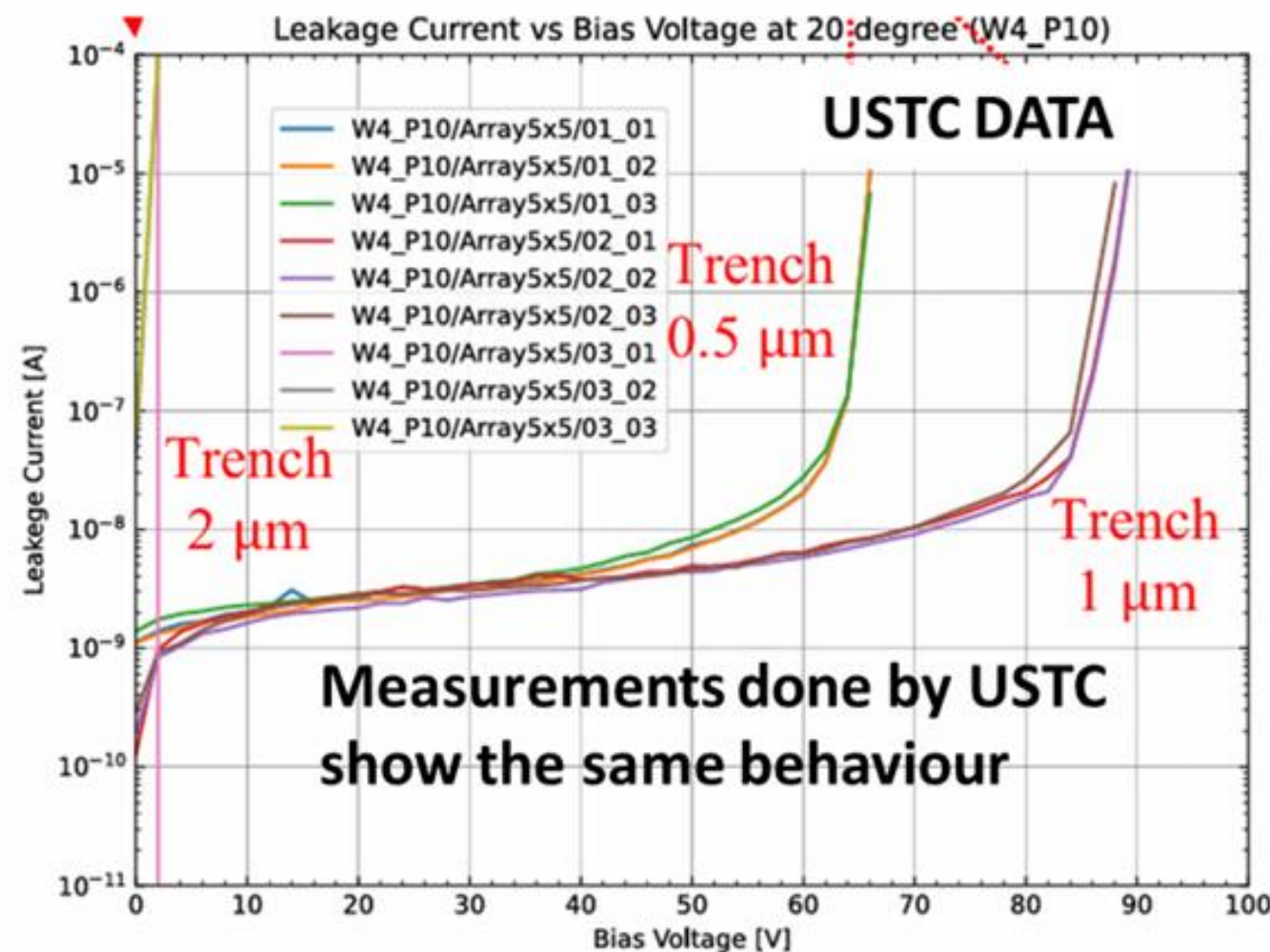
We clearly see the gain:

- Gain appears at $\sim 40\text{V}$
- reaches $G \sim 3-4$ at 50V
- **Reaches $G \sim 8-10$ at 60V**
- Confirmed also with Sr90 measurements



We clearly see the gain these devices that comes from geometry only, unlike in LGADs where it is due to carefully tuned doping!

Reproducibility



Same structures measured at different groups (from several institutions within DRD3 Coll); **all show remarkable reproducibility** (few measured at each institute all showing the same breakdown behaviour, both in charge collection and leakage current)

→ **That shows really good control of the process!**
There are also 25x25 mm² array currently being tested also in the test beam – see test beam talk

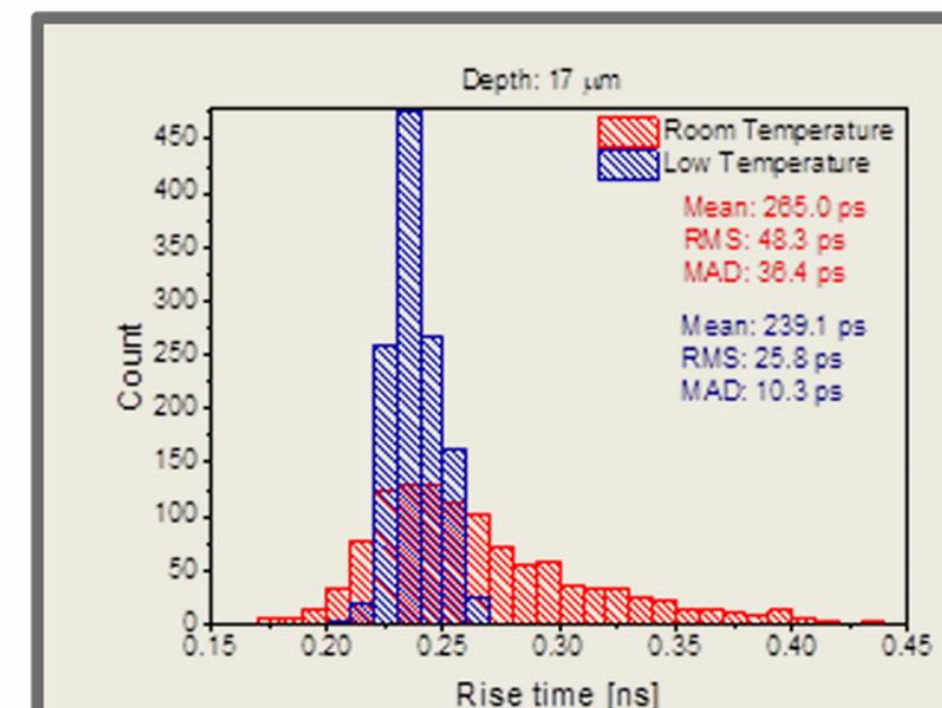
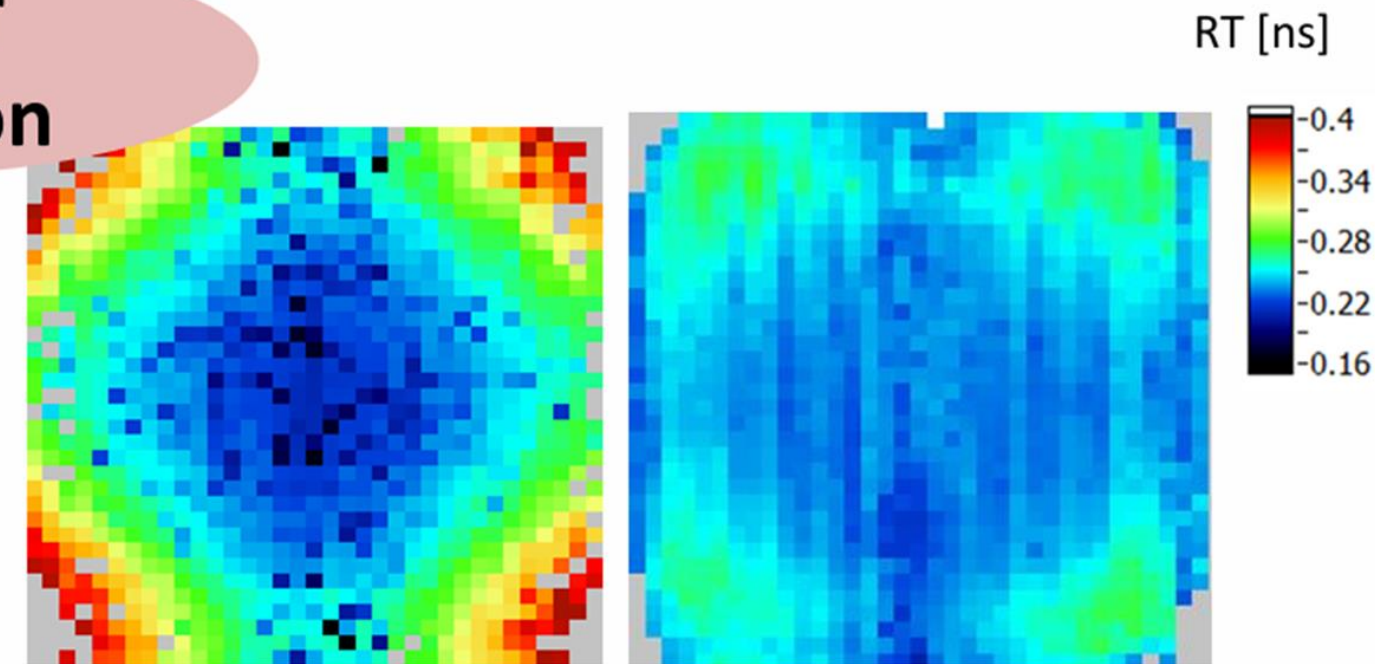
Example: Timing before and after irradiation

RT after
irradiation

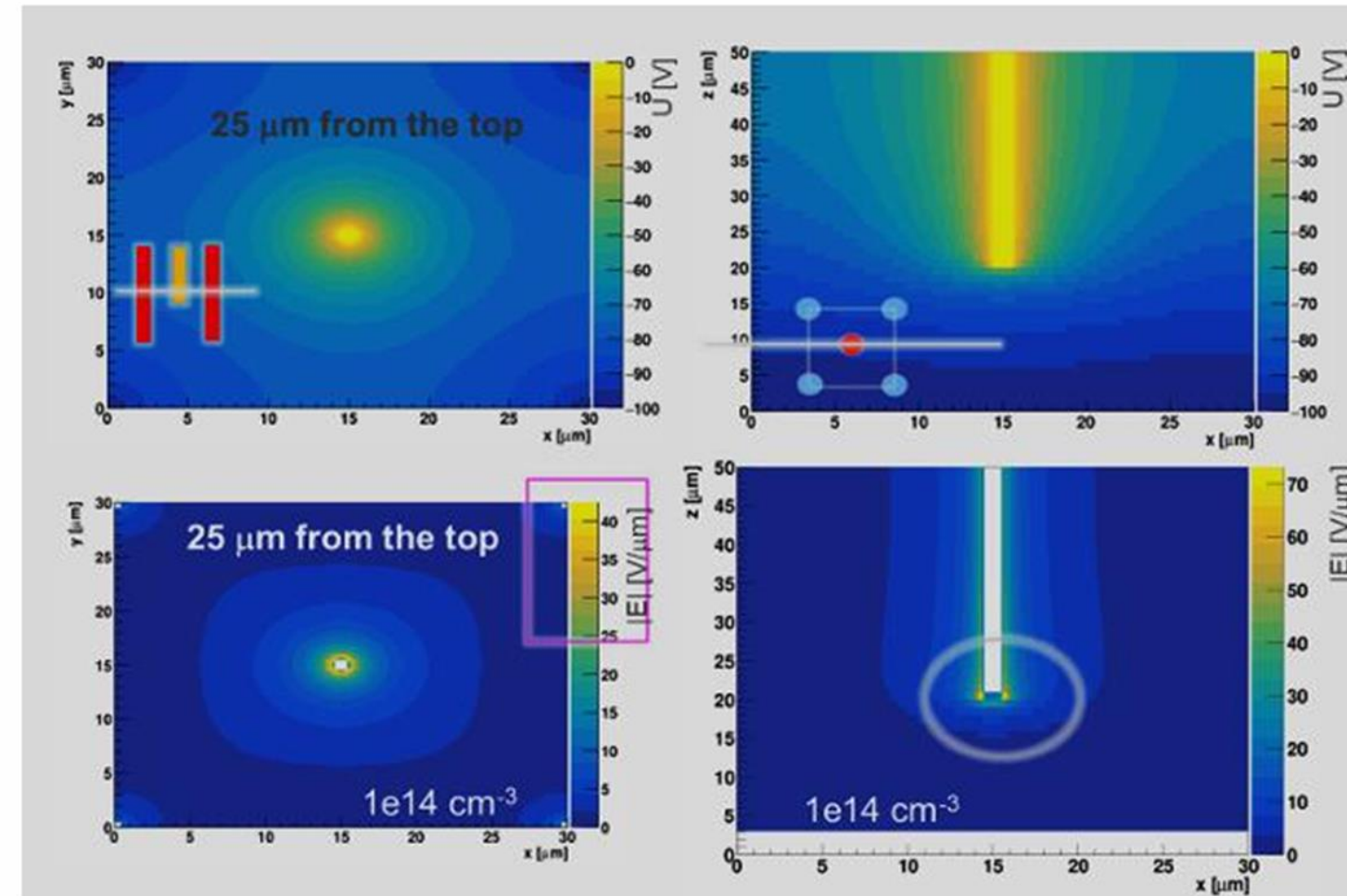
2D image
of Rise
Time

- ✓ at RT
- ✓ -25°C

RMS, MAD
(Rise Time)
✓ at RT (red)
✓ -25°C (blue)



What was learnt before?



We have learnt from previous 3D productions that electric field at the tip can be a big problem:

- simulations are clear
- we have observed increase of noisy pixels in ATLAS and CMS 3D pixel detectors at higher bias voltages what was clearly linked to distance of the tip to the substrate

We assumed that would be even larger problem for small column 3D detector as field focusing will be even larger:

- larger increase of the field wrt to the rest of the column – earlier breakdown
- Lots of variation of the breakdown performance as the tip is hard to control

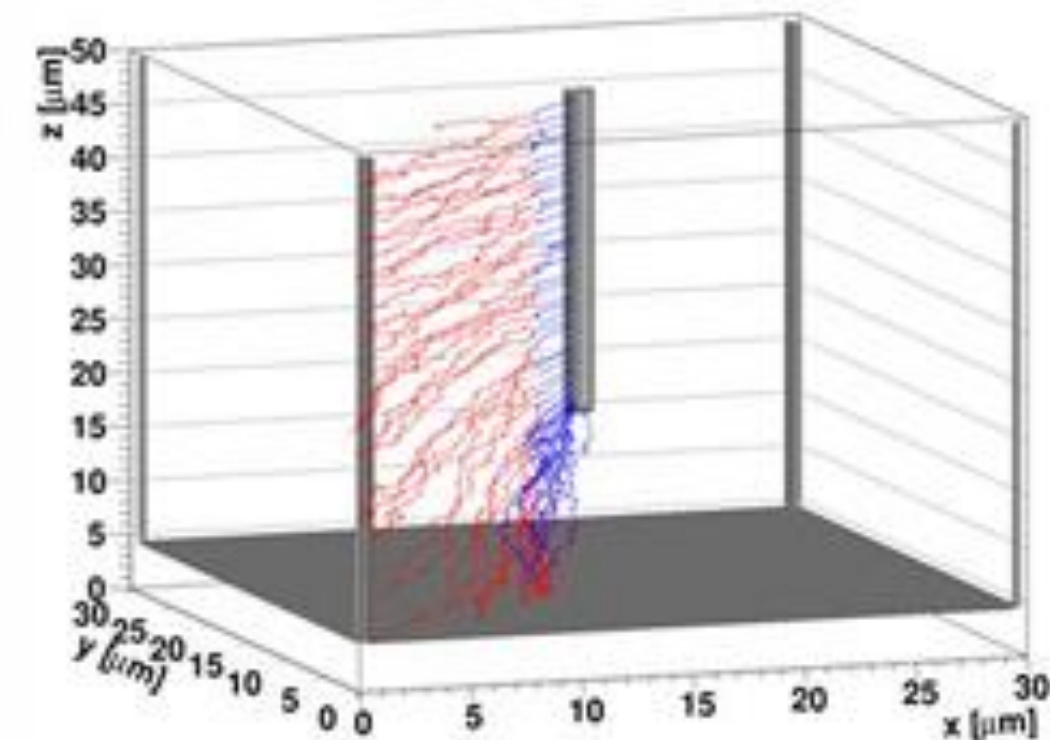
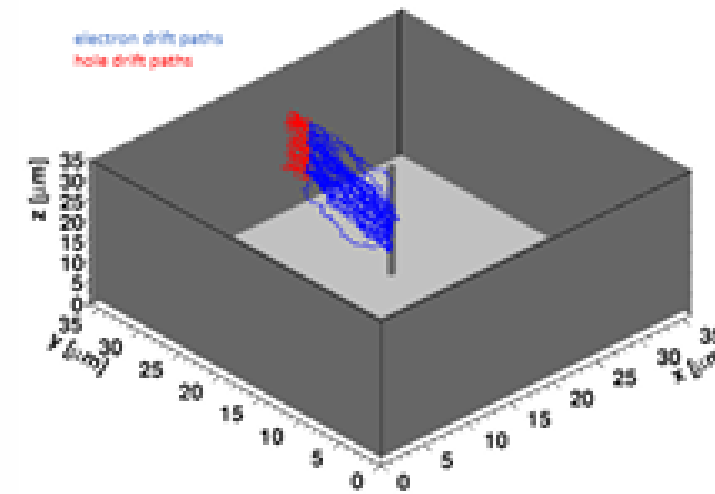
This turned out not to be the case and sensors perform with controllable gain and I-V/Gain-V performance is similar for all.

33

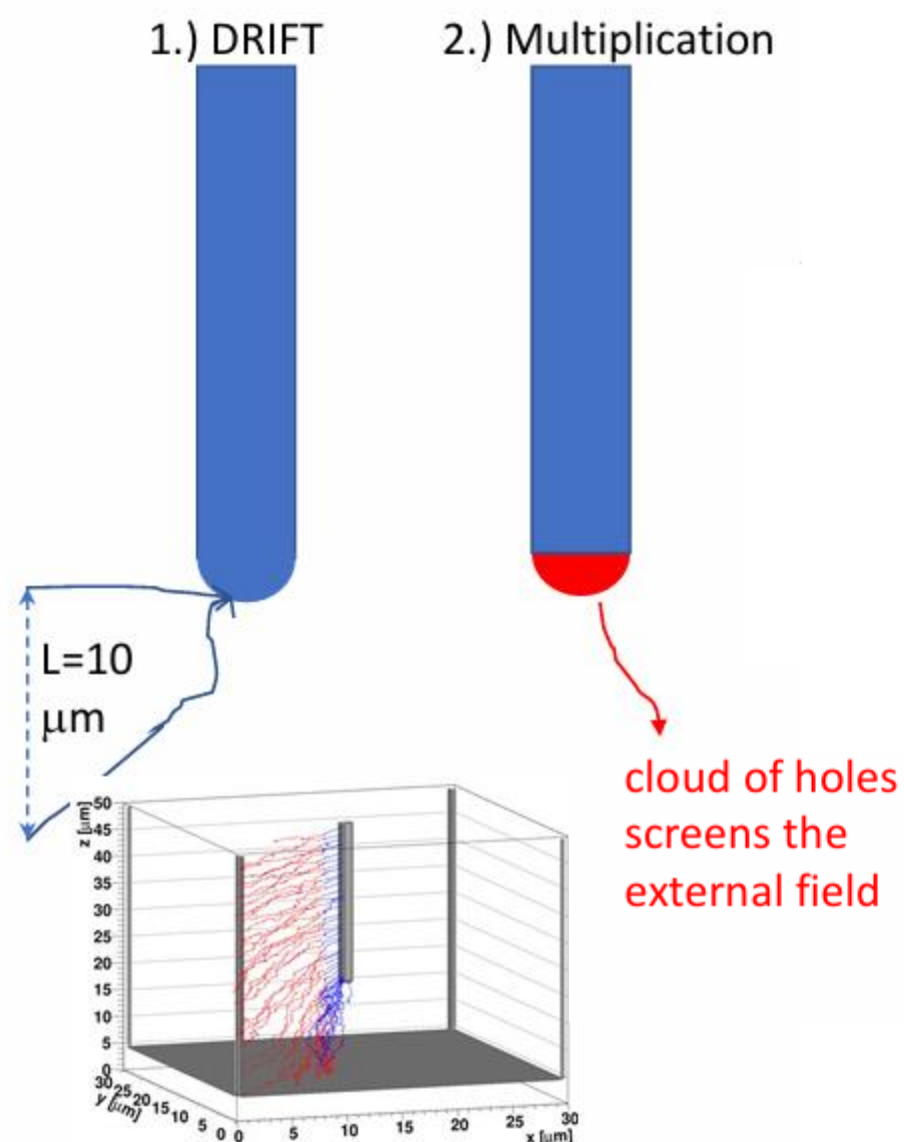
Surprised observed

We don't see increase of ghost rates generated at break-down close to the tip

- We don't see large variation of the charge with depth (~20%) even though more charges end the drift at the tip of the electrode (**next slide**)
- We see good agreement between Time of Arrival (ToA) in Two Photon Absorption TCT (TPA-TCT, characterization technique) and simulations— clearly the structure is not optimized for timing as it is now (trench cell is not optimum)



Advantage of small tip



If we assume charges are generated at the tip of the column with the gain=10
The tip is a (half) sphere so in the first approximation an elementary charge at the distance of the tip radius ($r=0.5 \mu\text{m}$) creates the field of

$$E_0 = \frac{e_0}{4\pi\epsilon\epsilon_0 r^2} \sim 5 \cdot 10^{-4} \text{ V}/\mu\text{m}$$

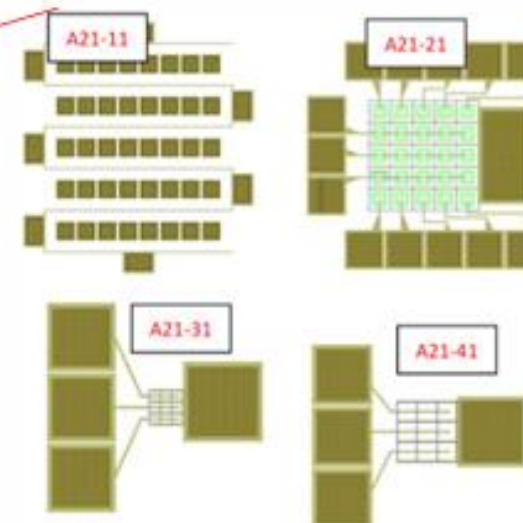
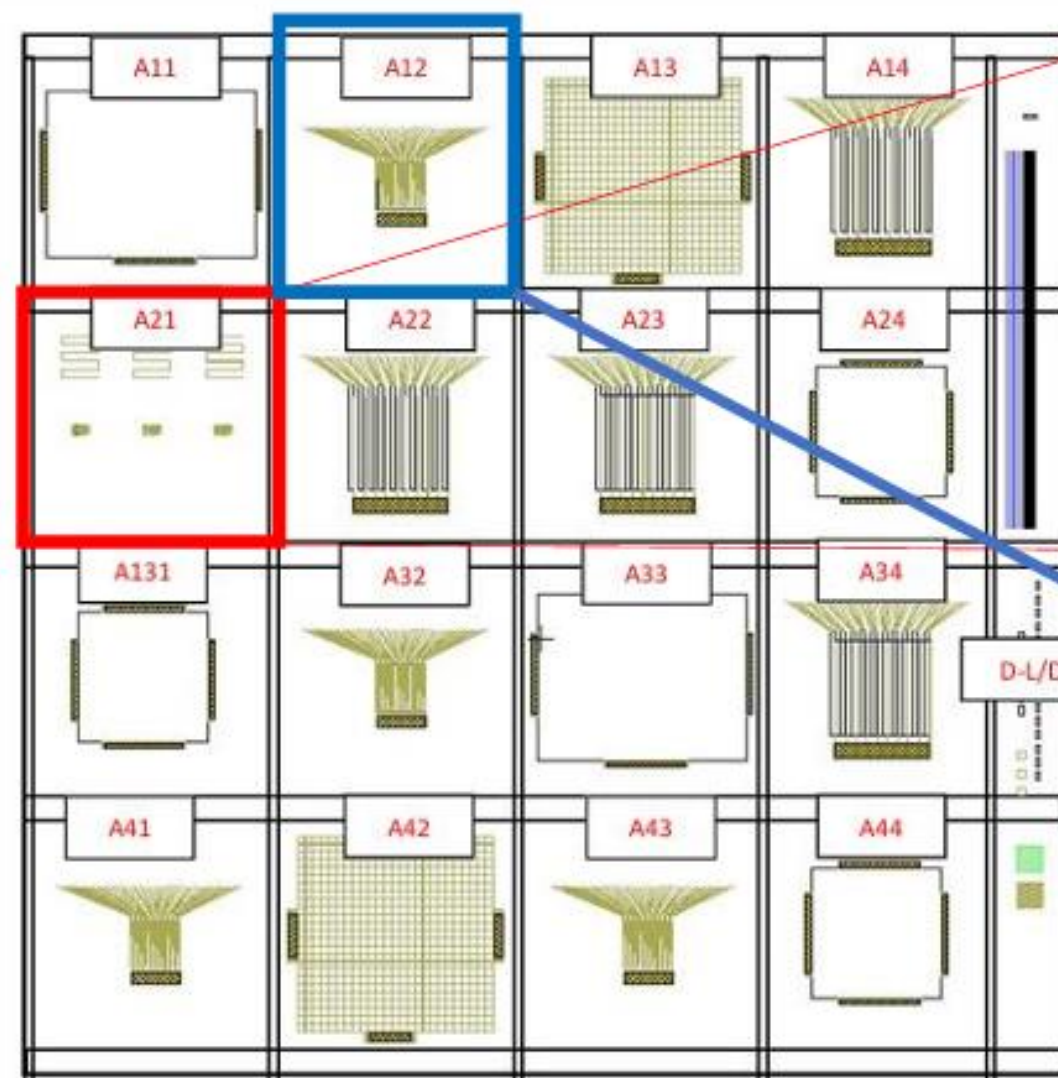
For $G=10$ and that taking charges from depth of around $L=10 \mu\text{m}$ and all come to the tip at the same time this means multiplied holes

$$\sim E_0 100 \frac{e-h}{\mu\text{m}} G * L \sim 5 \text{ V}/\mu\text{m} \quad (v_e \gg v_h)$$

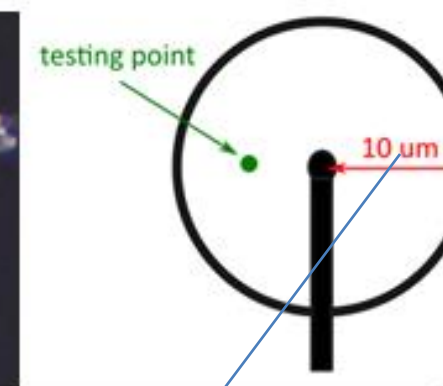
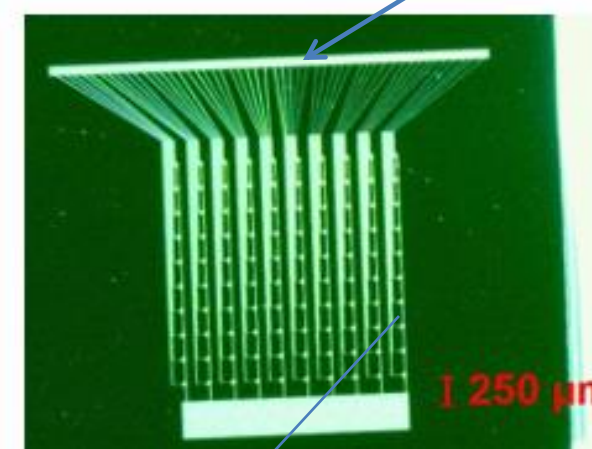
Sufficient for gain self-suppression

The structures – not intended for HEP purposes turned out to be very valuable

HEP structure – pixel detector

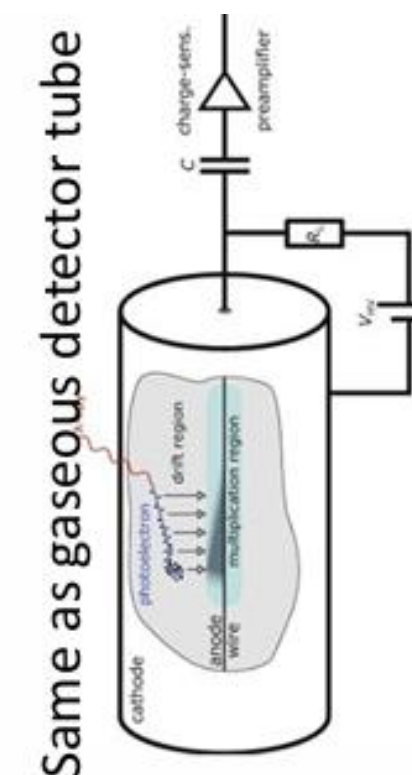


Non- HEP structures – array if tiny columns (straws)

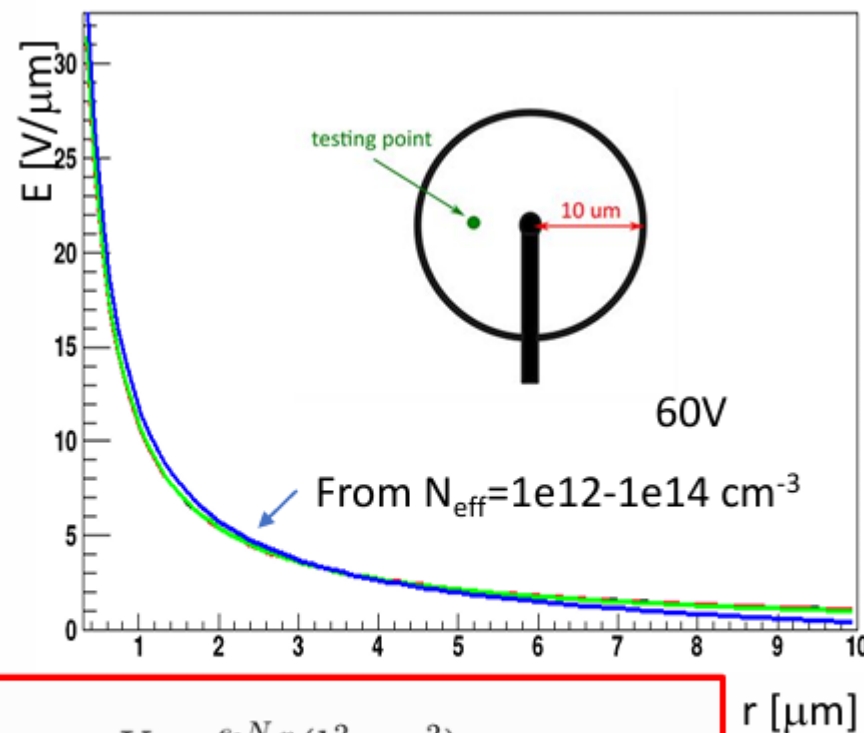


10x10 straw tubes!

Produced with diameters of 10 and 20 microns.

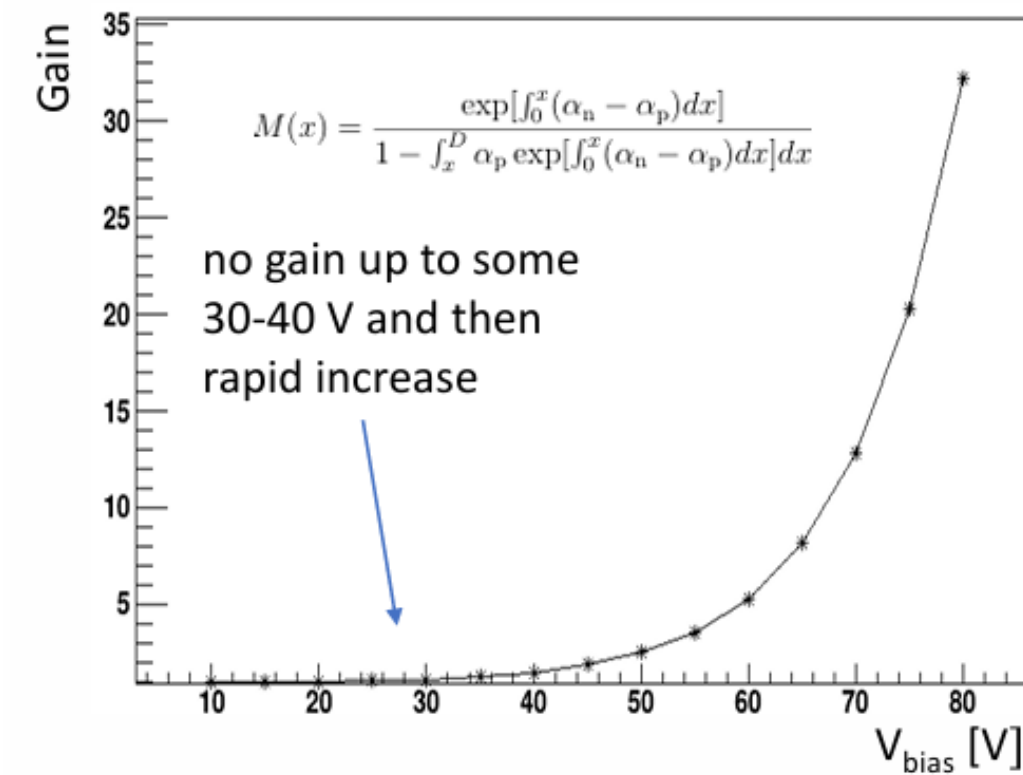


Ideal structures to study impact ionization – especially after irradiation – as the field can be solved analytically
Experimentally this is very complicated, but the project managed to do it– see next slide ! We will be able to study impact ionization at severe fluences.



$$E_r(r) = \frac{V_0 - \frac{e_0 N_{\text{eff}}}{4\epsilon\epsilon_0} (b^2 - a^2)}{r \ln(b/a)} + \frac{e_0 N_{\text{eff}} r}{2\epsilon\epsilon_0}$$

$a=0.5 \mu\text{m}$ and $b=10 \mu\text{m}$



Calculated gain as a function of bias voltage (V)

At the $z=15 \text{ mm}$ one can calculate analytically the gain – so fitting and extraction of impact ionization is straightforward

Outlook for the future

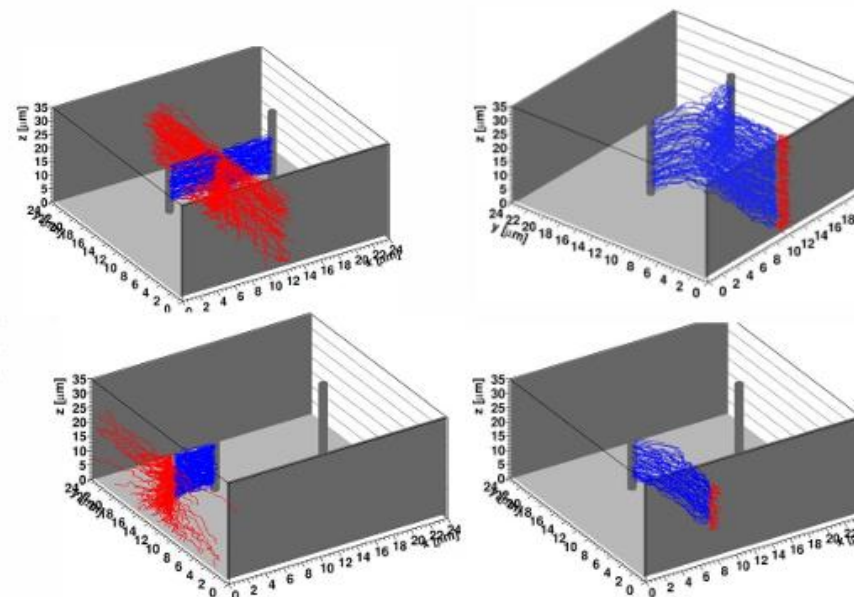
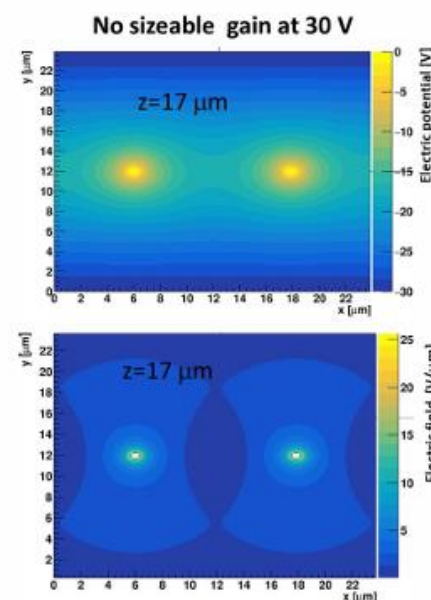
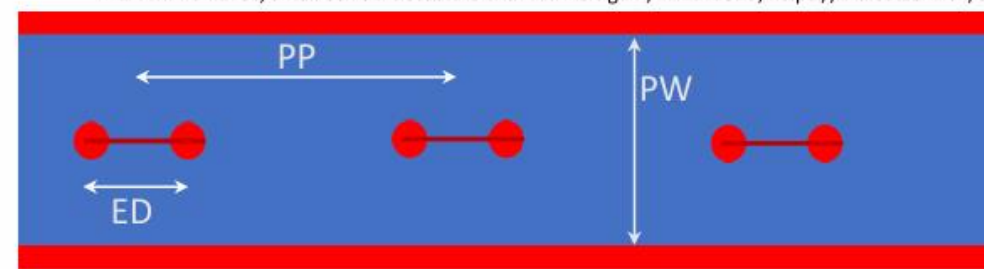


Outlook for the future

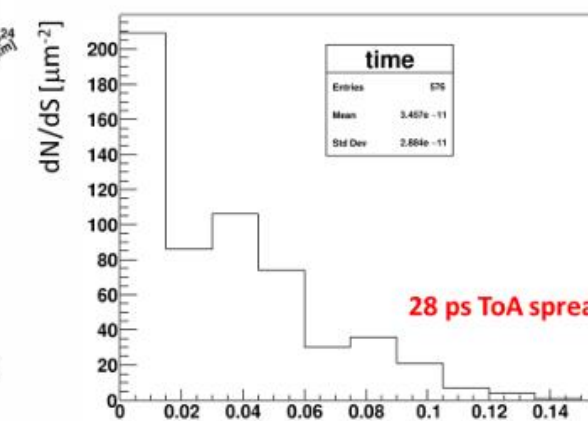
DRD

REF: M. Pukavec, Small cell 3D detectors with intrinsic gain, TREDI2026; <https://indico.cern.ch/event/1586892/contributions/6846212>

Optimization parameters:
PP – pixel pitch
PW – pixel width
ED – electrode distance
PT - Thickness



PP=24 μm, ED=12 μm,
PW=24 μm, PT=35 μm



3D detectors with gain for 4D tracking, 4th DRD3 week

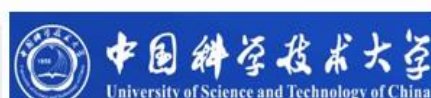
Conclusions:

- First very small pitch and thickness 3D devices were produced with controllable gain (35x35x35 mm³ cells)
- gains of up to around 10 were measured with devices fully functional at moderate voltages 62 V
- only a small gain variation across the cell was observed
- Devices were not optimized for timing and their timing performance is not excellent:
 - weighting field (distortion) contribution dominates the timing resolution
 - rise time variation across the cell can lead to jitter variations
- Time resolution is not yet fully understood both in Sr90 and TB
- Single cell cylindrical devices were produced ideal to study e.g. impact ionization as well as runaway trench devices
- New runs are planned to address devices for timing (2 runs within the project with IME until the end of 2027)
 - Design and fabrication of novel 3D sensor structures based on EPI wafer;
 - Design and fabrication of novel 3D sensor structures based on thick silicon wafer;
 - Design and fabrication of large area 3D trench-column sensors based on EPI wafer.

This project has received funding from

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- National Natural Science Foundation of China under Grant 12375188 and in part by the National Key Research and Development Program of China under Grant 2023YFF0719600.
- The European Union’s Horizon Europe Research and Innovation programme under Grant Agreement No 101057511 (EURO-LABS)

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Acknowledgements

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Thank you ☺